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1449A/PTO Rev. 10/95			S. Department of Commerce Patent and Trademark Office	Complete If Known		
TOTAL STATE OF THE			Color of the Color	Application Number		
LIST OF PRIOR ART CITED BY APPLICANT (use as many sheets as necessary)				Filing Date	03-23-04	
				First Named Inventor	Douglas James Tweet	
				Group Art Unit		
				Examiner Name		
Sheet	1	of	1	Attorney Docket No.	SLA.0586	

OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS							
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	L3				
WHL		HARRISON ET AL., Highly performant double gate MOSFET realized with SON process, IEDM 03-449, p18.6.1 (2003)					
WIL		YIN, ET AL., Strain relaxation of SiGe islands on compliant oxides, J. Appl. Phys. 91, p. 9716 (2002).					
SLL		R. CHAU ET AL., A 50nm Depleted-Substrate CMOS Transistor, IEDM, p. 621, 2001.					
WIC		TEZUKA ET AL., A Novel Fabrication Technique of Ultrathin and Relaxed SiGe Buffer Layers with High Ge Fraction for Sub-100nm Strained Silicon-on-Insulator MOSFETs, Jpn. J. Appl. Phys. 40, p. 2866 (2001)					
WIL		M. JURCZAK, ET AL., Silicon-on-Nothing (SON) - an innovative Process for Advanced CMOS, IEEE Trans. El. Dev. Vol. 47, pp2179-2187 (2000).					
WLL		MIZUNO ET AL., Advanced SOI-MOSFETs with strained-Si channel for high speed CMOS - electron/hole mobility enhancements, 2000 Symposium on VLSI, p. 210.					
WL		TRINKAUS ET AL., Strain relaxation mechanism for hydrogen-implanted Si _{1-x} Ge ₄ /Si (100) heterostructures, Appl. Phys. Lett., 76, p. 3552, (2000).					
ML		M. JURCZAK ET AL., SON (Silicon on Nothing) - A New Device Architecture for the ULSI Era, VLSI Tech. Dig., p.29, (1999).					
MU		R. KOH, Buried Layer Engineering to Reduce the Drain-Induced Barrier Lowering of Sub-0.05um SOI-MOSFET Jpn. J. Appl. Phys., Vol. 38, P. 2294 (1999)					
WLL		MANTL ET AL., Strain relaxation of epitaxial SiGe layers on Si (100) improved by hydrogen implantation, Nuclear Instruments and Methods in Physics Research B 147, p. 29, (1999)					
VLL		PAUL, Silicon germanium heterostructures in electronics: the present and the future, Thin Solid Films, 321, p. 172 (1998)					
WLL		RIM ET AL., Transconductance enhancement in deep submicron strained-Si n-MOSFETs, IEDM Proc. p. 707 (1998)					
WLL		WELSER ET AL., Electron mobility enhancement in strained-Si N-type metal-oxide-semiconductor field-effect transistors, IEEE EDL-15, #3, p.100, (1994)					
Wif		RIM ET AL., Enhanced hole mobilities in surface-channel strained-Si p-MOSFETs, IEDM Proc. p. 517 (1995)					

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Examiner Signature	Walk I.	Lowly	/ ·	Date Considered	6/2/2005

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